

Silicon NPN Power Transistors

2SC1051

DESCRIPTION

- With TO-3 package
- Wide area of safe operation

APPLICATIONS

- For low frequency power amplifier and large power switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

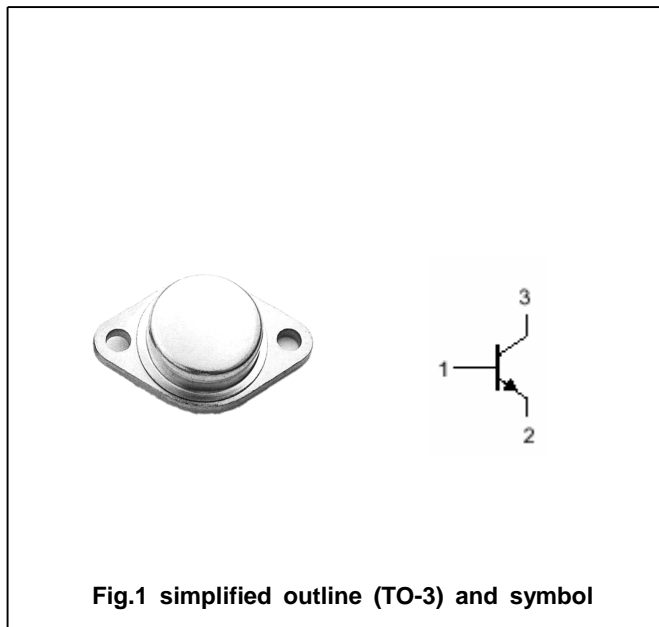


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		7	A
P_C	Collector power dissipation	$T_C=25^\circ$	60	W
T_j	Junction temperature		150	°
T_{stg}	Storage temperature		-55~150	°

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CHARACTERISTICS

T_j=25° unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A; I _B =0.5A			2.0	V
V _{BE}	Base-emitter on voltage	I _C =1A ; V _{CE} =5V			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =150V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	40		320	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =5V		8		MHz

U **h_{FE} Classifications**

C	D	E	F
40-80	60-120	100-200	160-320

PACKAGE OUTLINE

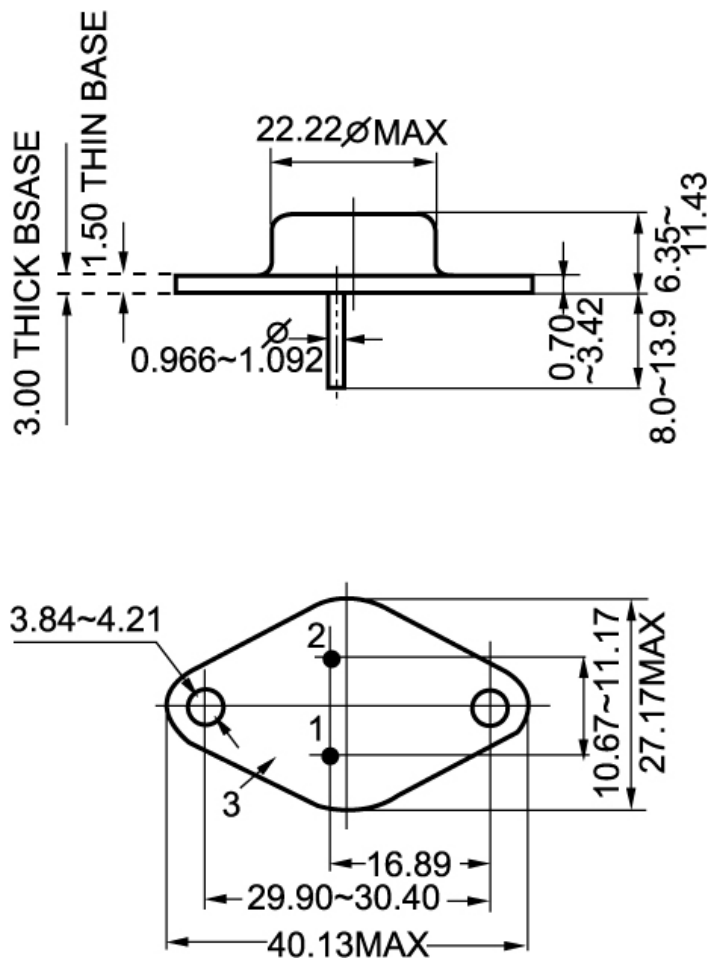


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)